

[查询"CQ220I-8BR"供应商](#)
centralTM
Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CQ220I-8BR
 CQ220I-8DR
 CQ220I-8MR
 CQ220I-8NR

ISOLATED TAB TRIAC
 8.0 AMP, 200 THRU 800 VOLTS

JEDEC TO-220AB CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CQ220I-8BR series type is an Epoxy Molded Silicon Triac designed for full wave AC control applications featuring gate triggering in all four (4) quadrants. This device is mounted in a TO-220 case with an isolated mounting tab.

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	CQ220I -8BR	CQ220I -8DR	CQ220I -8MR	CQ220I -8NR	UNITS
Peak Repetitive Off-State Voltage	V_{DRM}	200	400	600	800	V
RMS On-State Current ($T_C = 90^\circ\text{C}$)	$I_T(\text{RMS})$		8.0			A
Peak One Cycle Surge ($t = 10\text{ms}$)	I_{TSM}		80			A
I^2t Value for Fusing ($t = 10\text{ms}$)	I^2t		32			A^2s
Peak Gate Power ($t_p = 10\mu\text{s}$)	P_{GM}		40			W
Average Gate Power Dissipation	$P_{G(AV)}$		1.0			W
Peak Gate Current ($t_p = 10\mu\text{s}$)	I_{GM}		4.0			A
Peak Gate Voltage ($t_p = 10\mu\text{s}$)	V_{GM}		16			V
Critical Rate of Rise of On-State Current						
Repetitive ($F = 50\text{Hz}$)	di/dt		10			$\text{A}/\mu\text{s}$
Storage Temperature	T_{stg}		-40 to +150			$^\circ\text{C}$
Junction Temperature	T_J		-40 to +110			$^\circ\text{C}$
Thermal Resistance	θ_{J-A}		60			$^\circ\text{C}/\text{W}$
Thermal Resistance	θ_{J-C}		4.4			$^\circ\text{C}/\text{W}$
Isolation Voltage	V_{ISO}		2500			$V_{(\text{RMS})}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

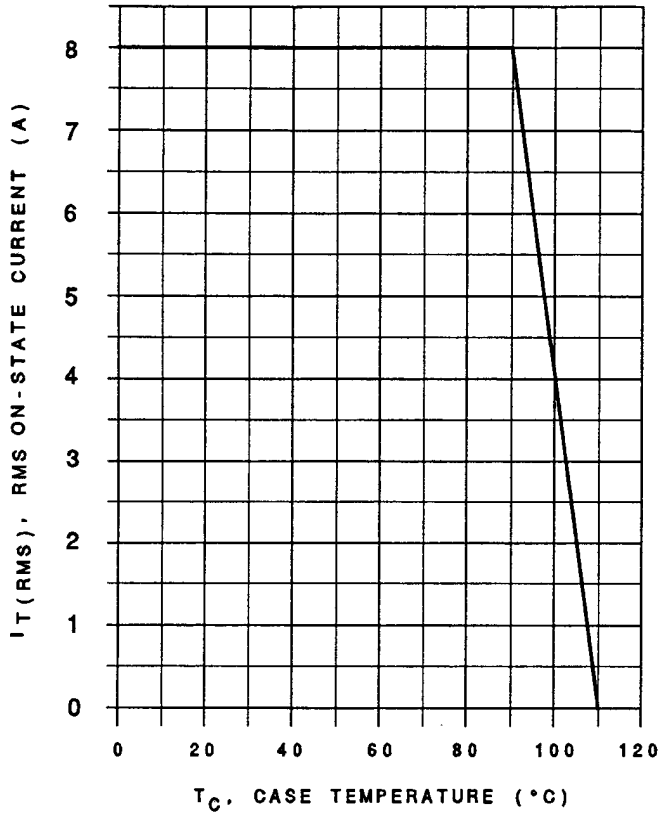
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DRM}	Rated V_{DRM}			0.01	mA
I_{DRM}	Rated V_{DRM} , $T_C = 110^\circ\text{C}$			0.75	mA
I_{GT}	$V_D = 12\text{V}$, $R_L = 33\Omega$, QUAD I,II,III			10	mA
I_{GT}	$V_D = 12\text{V}$, $R_L = 33\Omega$, QUAD IV			25	mA
I_H	$I_T = 100\text{mA}$			25	mA
V_{GT}	$V_D = 12\text{V}$, $R_L = 33\Omega$, QUAD I,II,III,IV			1.50	V
V_{TM}	$I_{TM} = 11\text{A}$, $t_p = 10\text{ms}$			1.75	V
dv/dt	$V_D = \frac{2}{3}V_{DRM}$, $R_{GK} = \infty$, $T_C = 110^\circ\text{C}$	10			$\text{V}/\mu\text{s}$

(OVER)

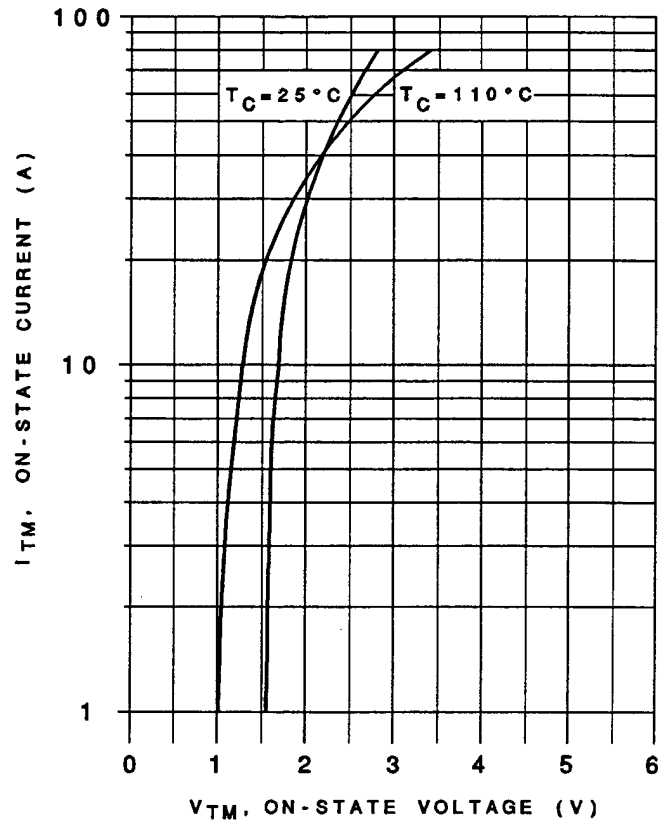
CQ220I-8BR SERIES RATING AND CHARACTERISTIC CURVES

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RMS ON-STATE CURRENT vs. CASE TEMPERATURE



MAXIMUM ON-STATE CHARACTERISTICS



MECHANICAL DIMENSIONS

All Dimensions in Inches (mm).

